Complementary Silicon High-Power Transistors

- . . . for general-purpose power amplifier and switching applications.
- 25 A Collector Current
- Low Leakage Current I_{CEO} = 1.0 mA @ 30 and 60 V
- Excellent DC Gain hFE = 40 Typ @ 15 A
- High Current Gain Bandwidth Product |hfe| = 3.0 min @ IC = 1.0 A, f = 1.0 MHz

MAXIMUM RATINGS

Rating	Symbol	TIP35A TIP36A	TIP35B TIP36B	TIP35C TIP36C	Unit
Collector–Emitter Voltage	VCEO	60 V	80 V	100 V	Vdc
Collector-Base Voltage	VCB	60 V	80 V	100 V	Vdc
Emitter-Base Voltage	VEB	- 500	5.0	Wa -	Vdc
Collector Current — Continuous Peak (1)	IC	25 40			Adc
Base Current — Continuous	ΙB	5.0			Adc
Total Power Dissipation @ T _C = 25°C Derate above 25°C	PD	125 1.0			Watts W/°C
Operating and Storage Junction Temperature Range	T _J , T _{stg}	-65 to +150			°C
Unclamped Inductive Load	ESB	90			mJ

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Case	R ₀ JC	1.0	°C/W
Junction-To-Free-Air Thermal Resistance	$R_{ heta JA}$	35.7	°C/W

(1) Pulse Test: Pulse Width = 10 ms, Duty Cycle ≤ 10%.

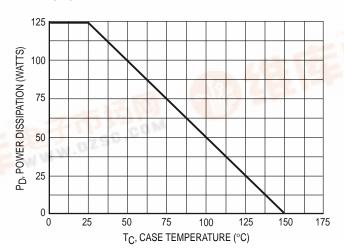


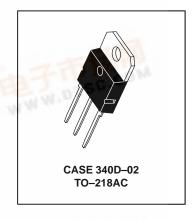
Figure 1. Power Derating

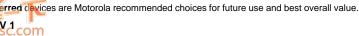
TIP35A
TIP35B*
TIP35C*
TIP36A
TIP36B*

NPN

TIP36C³
*Motorola Preferred Device

25 AMPERE
COMPLEMENTARY
SILICON
POWER TRANSISTORS
60-100 VOLTS
125 WATTS





ELECTRICAL CHARACTERISTICS (T_C = 25°C unless otherwise noted)

Characteristic		Symbol	Min	Max	Unit
OFF CHARACTERISTICS					
Collector–Emitter Sustaining Voltage (1) (I _C = 30 mA, I _B = 0)	TIP35A, TIP36A TIP35B, TIP36B TIP35C, TIP36C	VCEO(sus)	60 80 100	_ _ _	Vdc
Collector–Emitter Cutoff Current (VCE = 30 V, I _B = 0) (VCE = 60 V, I _B = 0)	TIP35A, TIP36A TIP35B, TIP35C, TIP36B, TIP36C	ICEO	_ _	1.0 1.0	mA
Collector–Emitter Cutoff Current (VCE = Rated VCEO, VEB = 0)		ICES	_	0.7	mA
Emitter–Base Cutoff Current (VEB = 5.0 V, I _C = 0)		IEBO	_	1.0	mA
ON CHARACTERISTICS (1)					•
DC Current Gain (I _C = 1.5 A, V _{CE} = 4.0 V) (I _C = 15 A, V _{CE} = 4.0 V)		hFE	25 15	— 75	_
Collector–Emitter Saturation Voltage (I _C = 15 A, I _B = 1.5 A) (I _C = 25 A, I _B = 5.0 A)		VCE(sat)		1.8 4.0	Vdc
Base–Emitter On Voltage (I _C = 15 A, V _{CE} = 4.0 V) (I _C = 25 A, V _{CE} = 4.0 V)		VBE(on)		2.0 4.0	Vdc
DYNAMIC CHARACTERISTICS					
Small–Signal Current Gain ($I_C = 1.0 \text{ A}, V_{CE} = 10 \text{ V}, f = 1.0 \text{ kHz}$)		h _{fe}	25	_	_
Current-Gain — Bandwidth Product (I _C = 1.0 A, V _{CE} = 10 V, f = 1.0 MHz)		fΤ	3.0	_	MHz

⁽¹⁾ Pulse Test: Pulse Width = 300 μs , Duty Cycle \leq 2.0%.

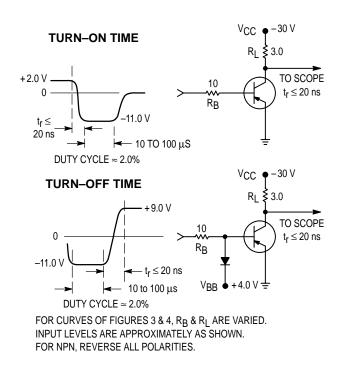


Figure 2. Switching Time Equivalent Test Circuits

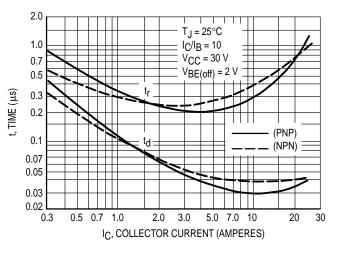


Figure 3. Turn-On Time

A L DI L D. T. LL D.

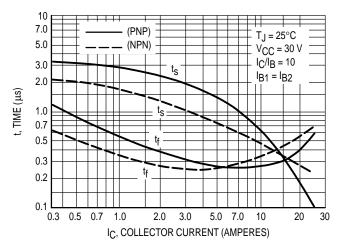


Figure 4. Turn-Off Time

FORWARD BIAS

There are two limitations on the power handling ability of a transistor: average junction temperature and second breakdown. Safe operating area curves indicate IC – VCE limits of the transistor that must be observed for reliable operation; i.e., the transistor must not be subjected to greater dissipation than the curves indicate.

The data of Figure 6 is based on $T_C = 25^{\circ}C$; $T_{J(pk)}$ is variable depending on power level. Second breakdown pulse limits are valid for duty cycles to 10% but must be derated when $T_C \ge 25^{\circ}C$. Second breakdown limitations do not derate the same as thermal limitations.

REVERSE BIAS

For inductive loads, high voltage and high current must be sustained simultaneously during turn-off, in most cases, with the base to emitter junction reverse biased. Under these conditions the collector voltage must be held to a safe level at or below a specific value of collector current. This can be accomplished by several means such as active clamping, RC snubbing, load line shaping, etc. The safe level for these devices is specified as Reverse Bias Safe Operating Area and represents the voltage-current conditions during reverse biased turn-off. This rating is verified under clamped conditions so that the device is never subjected to an avalanche mode. Figure 7 gives RBSOA characteristics.

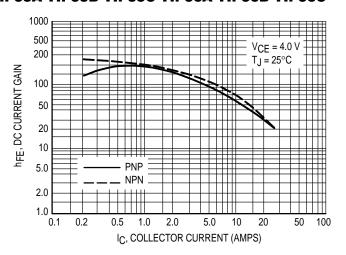


Figure 5. DC Current Gain

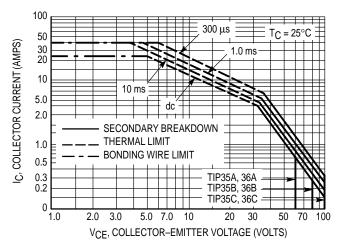


Figure 6. Maximum Rated Forward Bias Safe Operating Area

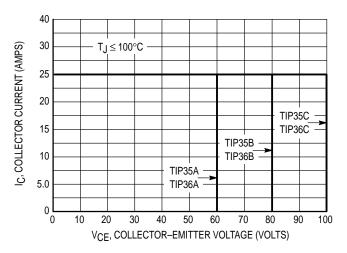
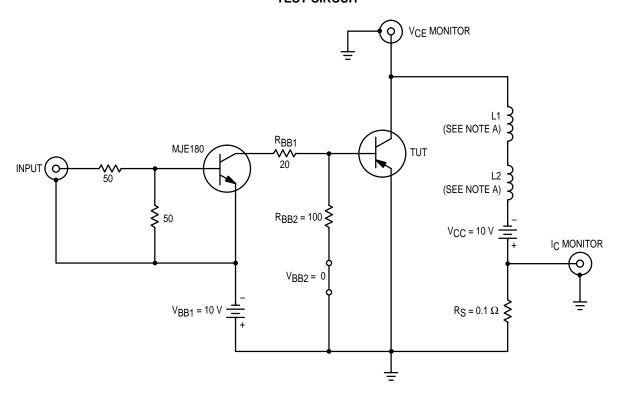
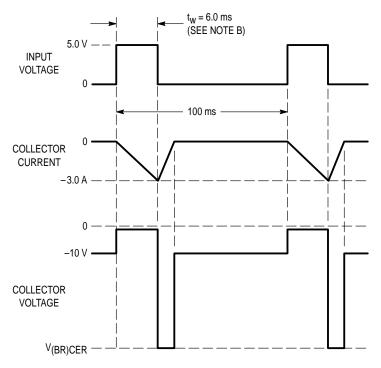


Figure 7. Maximum Rated Forward Bias Safe Operating Area

TEST CIRCUIT



VOLTAGE AND CURRENT WAVEFORMS



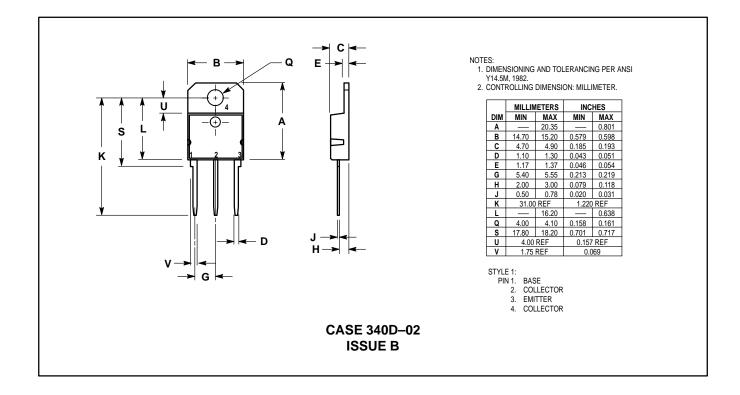
NOTES:

- A. L1 and L2 are 10 mH, 0.11 Ω , Chicago Standard Transformer Corporation C–2688, or equivalent.
- B. Input pulse width is increased until $I_{CM} = -3.0 \text{ A}$.
- C. For NPN, reverse all polarities.

Figure 8. Inductive Load Switching

Maria Diagram

PACKAGE DIMENSIONS



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